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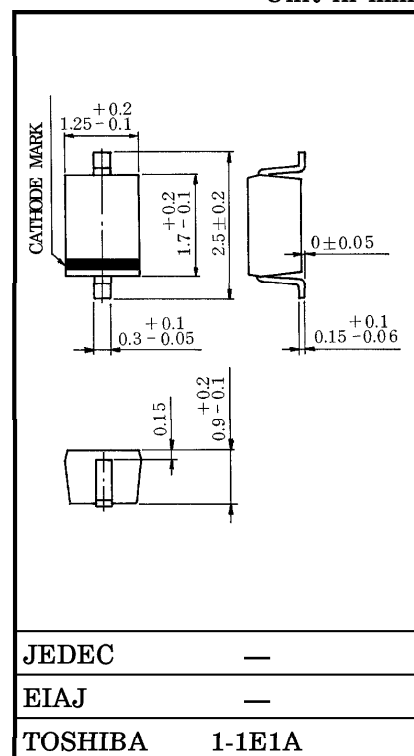
CATV TUNING.

- High Capacitance Ratio : $C_{2V} / C_{25V} = 11.5$ (Typ.)
- Low Series Resistance : $r_s = 0.55 \Omega$ (Typ.)
- Excellent C-V Characteristics, and Small Tracking Error.
- Small Package

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	V_R	34	V
Peak Reverse Voltage	V_{RM}	36 ($R_L = 10k\Omega$)	V
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55 \sim 125$	$^\circ\text{C}$

Unit in mm

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	V_R	$I_R = 1\mu\text{A}$	34	—	—	V
Reverse Current	I_R	$V_R = 32\text{V}$	—	—	10	nA
Capacitance	C_{2V}	$V_R = 2\text{V}, f = 1\text{MHz}$	29	31.5	34	pF
Capacitance	C_{25V}	$V_R = 25\text{V}, f = 1\text{MHz}$	2.5	2.75	2.9	pF
Capacitance Ratio	C_{2V} / C_{25V}	—	11.0	11.5	—	—
Capacitance Ratio	C_{25V} / C_{28V}	—	1.03	1.05	—	—
Series Resistance	r_s	$V_R = 5\text{V}, f = 470\text{MHz}$	—	0.55	0.7	Ω

Note 1 : Available in matched group for capacitance to 2.0%.

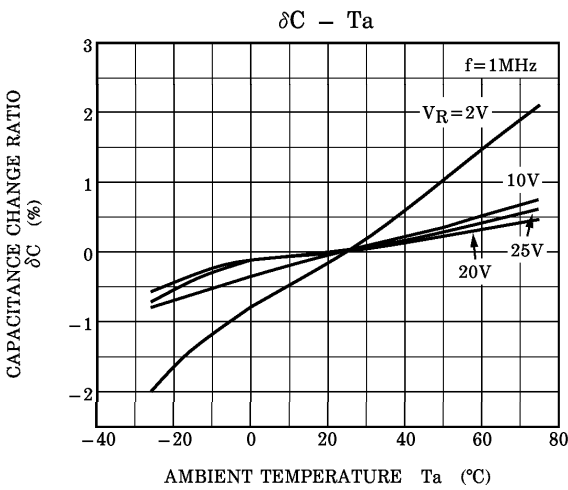
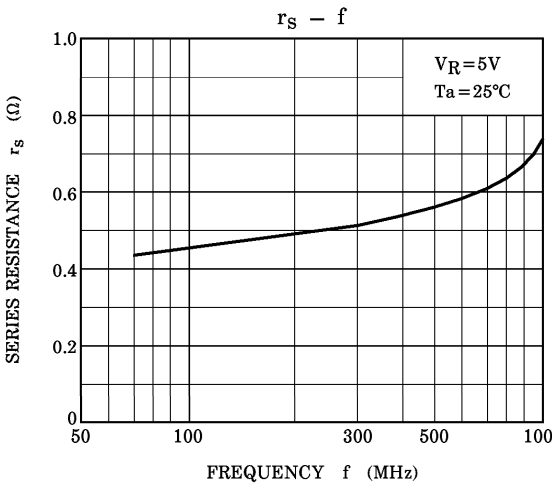
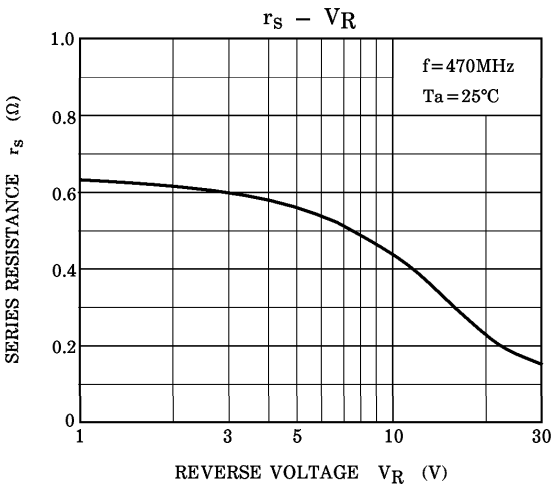
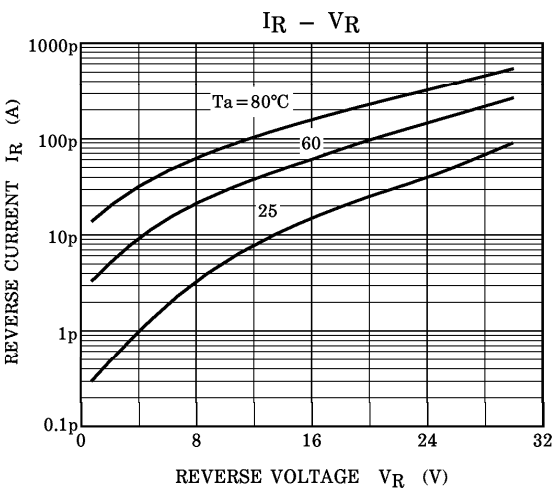
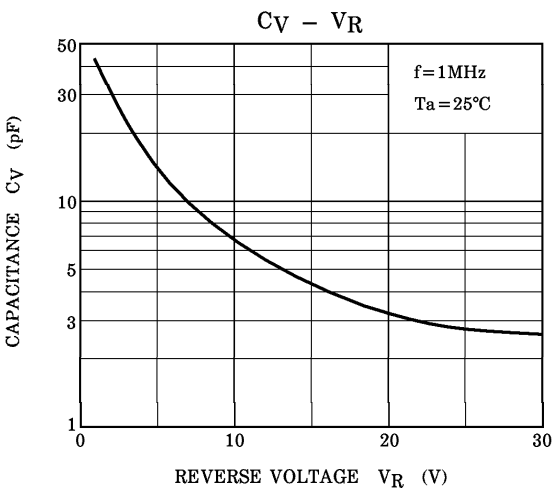
$$\frac{C(\text{Max.}) - C(\text{Min.})}{C(\text{Min.})} \leq 0.02 \quad (V_R = 2 \sim 25\text{V})$$

Marking



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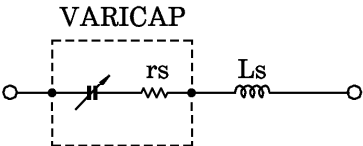
SPICE PARAMETER

SPICE MODEL : BERKLEY SPICE.2G.6 DIODE MODEL
DATA FORMAT : MODEL FORMAT
SPICE SYMBOL : I_S (A), R_S (Ω), N (-), $CJ0$ (F), V_J (V), M (-), B_V (V), I_{BV} (A)
FREQUENCY RANGE : $f = 0.1 \sim 3$ GHz
REVERSE VOLTAGE RANGE : $V_R = 2 \sim 25$ V

PARAMETER

$I_S = 6.685E - 15$
 $N = 1.069$
 $B_V = 34$
 $I_{BV} = 1.00E - 06$
 $R_S = 0.55$
 $CJ0 = 6.847E - 11$
 $V_J = 2.378$
 $M = 1.356$

 $L_s = 1.00E - 09$



- (Note 1) : These parameters from I_S to M mean die characteristic.
 Actually device has lead inductance so L_s is necessary for simulation.
 And please use default value except above parameters.
- (Note 2) : R_S shows the value at the condition of $V_R = 5$ V and $f = 470$ MHz.
 If another value is needed, please refer to $R_S - V_R$ curve in this data sheets.